

DATA SHEET

PDTA123E series

PNP resistor-equipped transistors;

R1 = 2.2 k Ω , R2 = 2.2 k Ω

Product data sheet
Supersedes data of 2004 Apr 07

2004 Aug 02

PNP resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 2.2 k Ω

PDTA123E series

FEATURES

- Built-in bias resistors
- Simplified circuit design
- Reduction of component count
- Reduced pick and place costs.

APPLICATIONS

- General purpose switching and amplification
- Inverter and interface circuits
- Circuit driver.

QUICK REFERENCE DATA

SYMBOL	PARAMETER	TYP.	MAX.	UNIT
V _{CEO}	collector-emitter voltage	–	–50	V
I _O	output current (DC)	–	–100	mA
R1	bias resistor	2.2	–	k Ω
R2	bias resistor	2.2	–	k Ω

DESCRIPTION

PNP resistor-equipped transistor (see “Simplified outline, symbol and pinning” for package details).

PRODUCT OVERVIEW

TYPE NUMBER	PACKAGE		MARKING CODE	NPN COMPLEMENT
	PHILIPS	EIAJ		
PDTA123EE	SOT416	SC-75	5C	PDTC123EE
PDTA123EEF	SOT490	SC-89	6C	PDTC123EEF
PDTA123EK	SOT346	SC-59	42	PDTC123EK
PDTA123EM	SOT883	SC-101	F7	PDTC123EM
PDTA123ES	SOT54 (TO-92)	SC-43	TA123E	PDTC123ES
PDTA123ET	SOT23	–	*21 ⁽¹⁾	PDTC123ET
PDTA123EU	SOT323	SC-70	*42 ⁽¹⁾	PDTC123EU

Note

1. * = p: Made in Hong Kong.
* = t: Made in Malaysia.
* = W: Made in China.

PNP resistor-equipped transistors;
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PDTA123E series

SIMPLIFIED OUTLINE, SYMBOL AND PINNING

TYPE NUMBER	SIMPLIFIED OUTLINE AND SYMBOL	PINNING	
		PIN	DESCRIPTION
PDTA123ES	<p>MAM338</p>	1 2 3	base collector emitter
PDTA123EE PDTA123EEF PDTA123EK PDTA123ET PDTA123EU	<p>Top view</p> <p>MDB271</p>	1 2 3	base emitter collector
PDTA123EM	<p>Bottom view</p> <p>MDB267</p>	1 2 3	base emitter collector

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PDTA123E series

ORDERING INFORMATION

TYPE NUMBER	PACKAGE		
	NAME	DESCRIPTION	VERSION
PDTA123EE	–	plastic surface mounted package; 3 leads	SOT416
PDTA123EEF	–	plastic surface mounted package; 3 leads	SOT490
PDTA123EK	–	plastic surface mounted package; 3 leads	SOT346
PDTA123EM	–	leadless ultra small plastic package; 3 solder lands; body 1.0 x 0.6 x 0.5 mm	SOT883
PDTA123ES	–	plastic single-ended leaded (through hole) package; 3 leads	SOT54
PDTA123ET	–	plastic surface mounted package; 3 leads	SOT23
PDTA123EU	–	plastic surface mounted package; 3 leads	SOT323

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CB0}	collector-base voltage	open emitter	–	–50	V
V _{CEO}	collector-emitter voltage	open base	–	–50	V
V _{EBO}	emitter-base voltage	open collector	–	–10	V
V _I	input voltage				
	positive		–	+10	V
	negative		–	–12	V
I _O	output current (DC)		–	–100	mA
I _{CM}	peak collector current		–	–100	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C			
	SOT54	note 1	–	500	mW
	SOT23	note 1	–	250	mW
	SOT346	note 1	–	250	mW
	SOT323	note 1	–	200	mW
	SOT416	note 1	–	150	mW
	SOT490	notes 1 and 2	–	250	mW
SOT883	notes 2 and 3	–	250	mW	
T _{stg}	storage temperature		–65	+150	°C
T _j	junction temperature		–	150	°C
T _{amb}	operating ambient temperature		–65	+150	°C

Notes

1. Refer to standard mounting conditions.
2. Reflow soldering is the only recommended soldering method.
3. Refer to SOT883 standard mounting conditions; FR4 with 60 μ m copper strip line.

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THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th(j-a)}	thermal resistance from junction to ambient	T _{amb} ≤ 25 °C		
	SOT54	note 1	250	K/W
	SOT23	note 1	500	K/W
	SOT346	note 1	500	K/W
	SOT323	note 1	625	K/W
	SOT416	note 1	830	K/W
	SOT490	notes 1 and 2	500	K/W
SOT883	notes 2 and 3	500	K/W	

Notes

1. Refer to standard mounting conditions.
2. Reflow soldering is the only recommended soldering method.
3. Refer to SOT883 standard mounting conditions; FR4 with 60 μ m copper strip line.

CHARACTERISTICS

T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I _{CBO}	collector-base cut-off current	V _{CB} = -50 V; I _E = 0 A	-	-	-100	nA
I _{CEO}	collector-emitter cut-off current	V _{CE} = -30 V; I _B = 0 A	-	-	-1	μ A
		V _{CE} = -30 V; I _B = 0 A; T _j = 150 °C	-	-	-50	μ A
I _{EBO}	emitter-base cut-off current	V _{EB} = -5 V; I _C = 0 A	-	-	-2	mA
h _{FE}	DC current gain	V _{CE} = -5 V; I _C = -20 mA	30	-	-	
V _{CEsat}	collector-emitter saturation voltage	I _C = -10 mA; I _B = -0.5 mA	-	-	-150	mV
V _{i(off)}	input-off voltage	I _C = -1 mA; V _{CE} = -5 V	-	-1.2	-0.5	V
V _{i(on)}	input-on voltage	I _C = -20 mA; V _{CE} = -0.3 V	-2	-1.6	-	V
R1	input resistor		1.54	2.2	2.86	k Ω
$\frac{R2}{R1}$	resistor ratio		0.8	1	1.2	
C _c	collector capacitance	I _E = i _e = 0 A; V _{CB} = -10 V; f = 1 MHz	-	-	3	pF

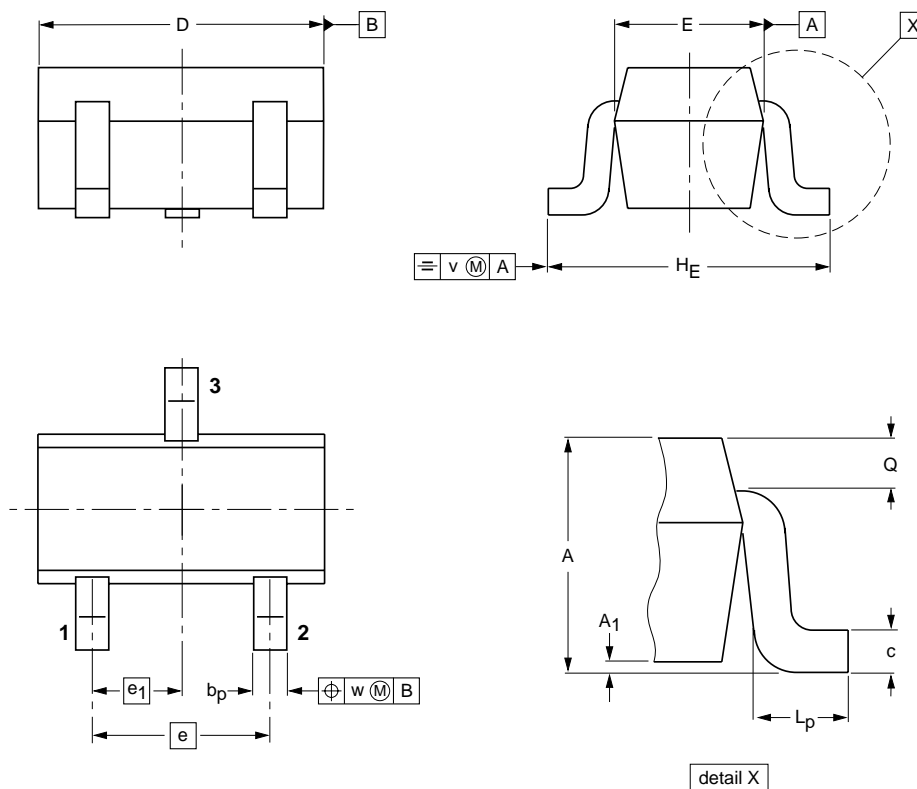
PNP resistor-equipped transistors;
R1 = 2.2 kΩ, R2 = 2.2 kΩ

PDTA123E series

PACKAGE OUTLINES

Plastic surface-mounted package; 3 leads

SOT416



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁ max	b _p	c	D	E	e	e ₁	H _E	L _p	Q	v	w
mm	0.95 0.60	0.1	0.30 0.15	0.25 0.10	1.8 1.4	0.9 0.7	1	0.5	1.75 1.45	0.45 0.15	0.23 0.13	0.2	0.2

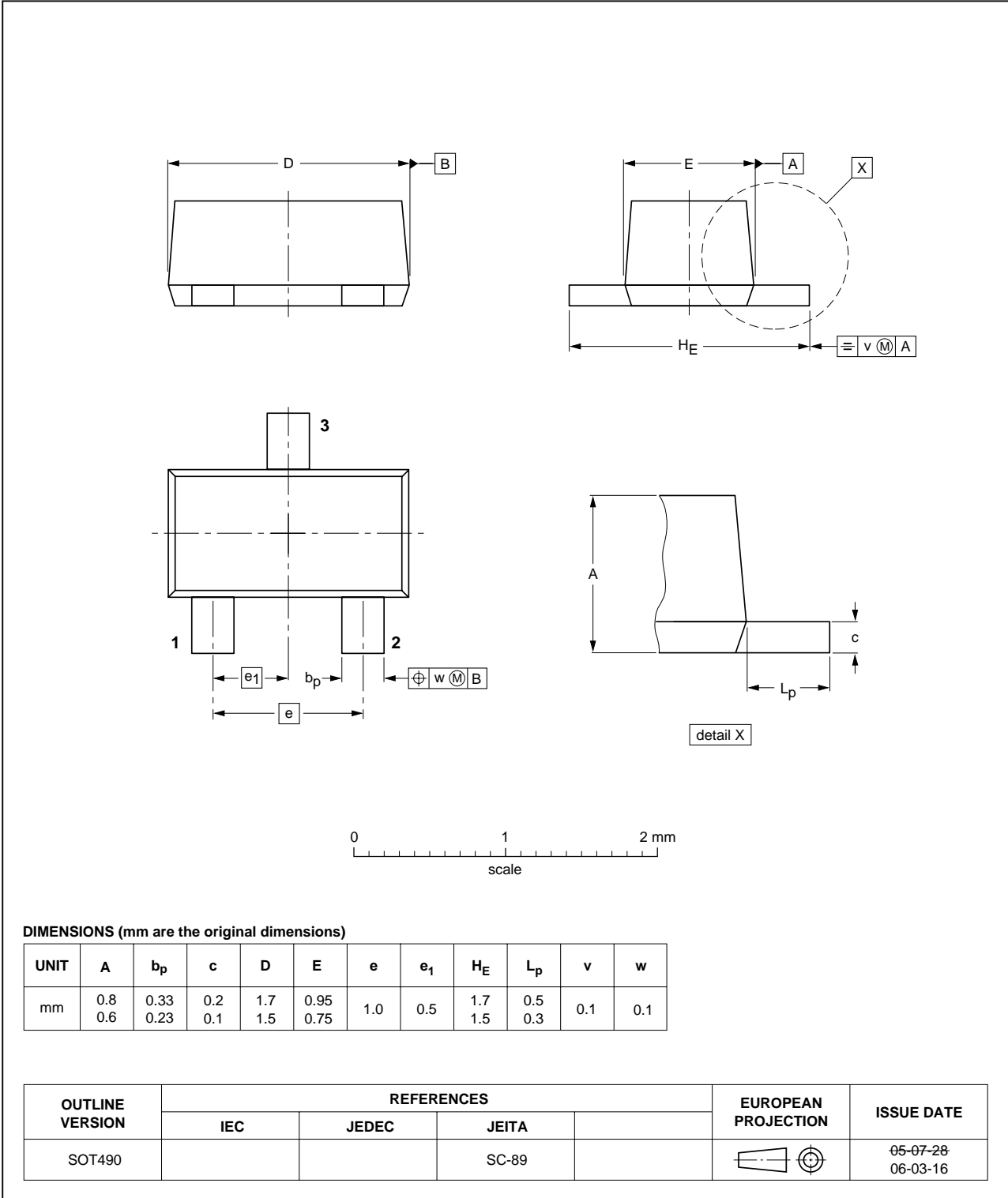
OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT416			SC-75			04-11-04 06-03-16

PNP resistor-equipped transistors;
R1 = 2.2 kΩ, R2 = 2.2 kΩ

PDTA123E series

Plastic surface-mounted package; 3 leads

SOT490

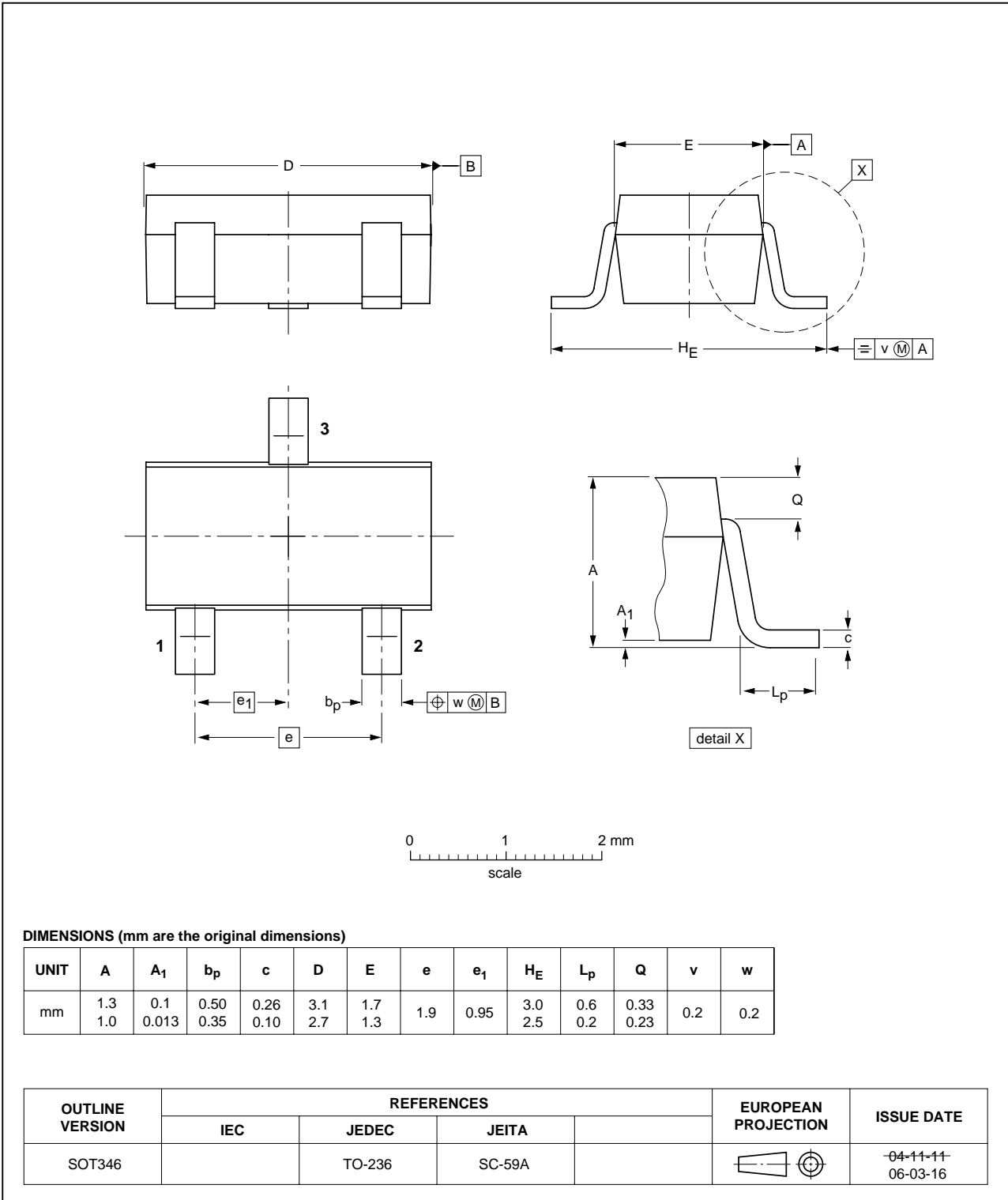


PNP resistor-equipped transistors;
R1 = 2.2 kΩ, R2 = 2.2 kΩ

PDTA123E series

Plastic surface-mounted package; 3 leads

SOT346

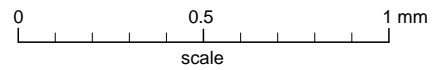
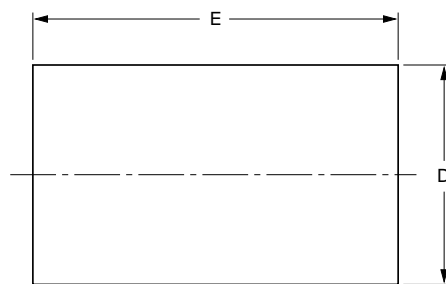
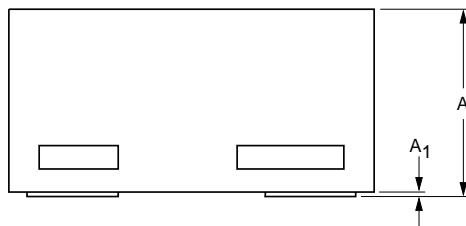
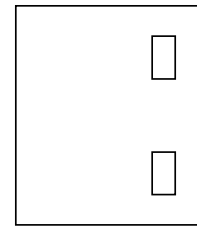


PNP resistor-equipped transistors;
R1 = 2.2 kΩ, R2 = 2.2 kΩ

PDTA123E series

Leadless ultra small plastic package; 3 solder lands; body 1.0 x 0.6 x 0.5 mm

SOT883



DIMENSIONS (mm are the original dimensions)

UNIT	A ⁽¹⁾	A ₁ max.	b	b ₁	D	E	e	e ₁	L	L ₁
mm	0.50 0.46	0.03	0.20 0.12	0.55 0.47	0.62 0.55	1.02 0.95	0.35	0.65	0.30 0.22	0.30 0.22

Note

1. Including plating thickness

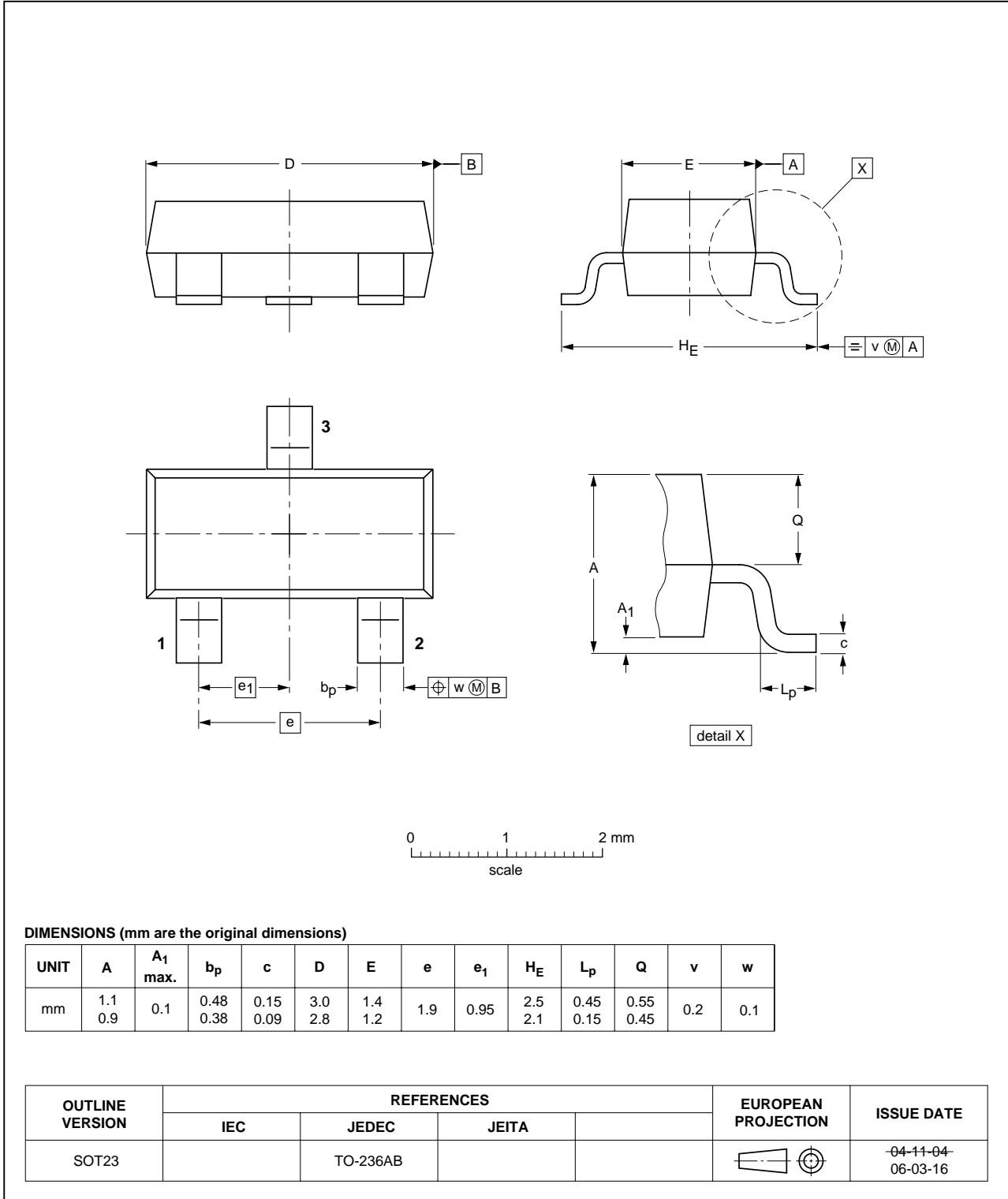
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	IEC	JEDEC	JEITA		
SOT883			SC-101		03-02-05 03-04-03

PNP resistor-equipped transistors;
R1 = 2.2 kΩ, R2 = 2.2 kΩ

PDTA123E series

Plastic surface-mounted package; 3 leads

SOT23

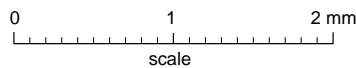
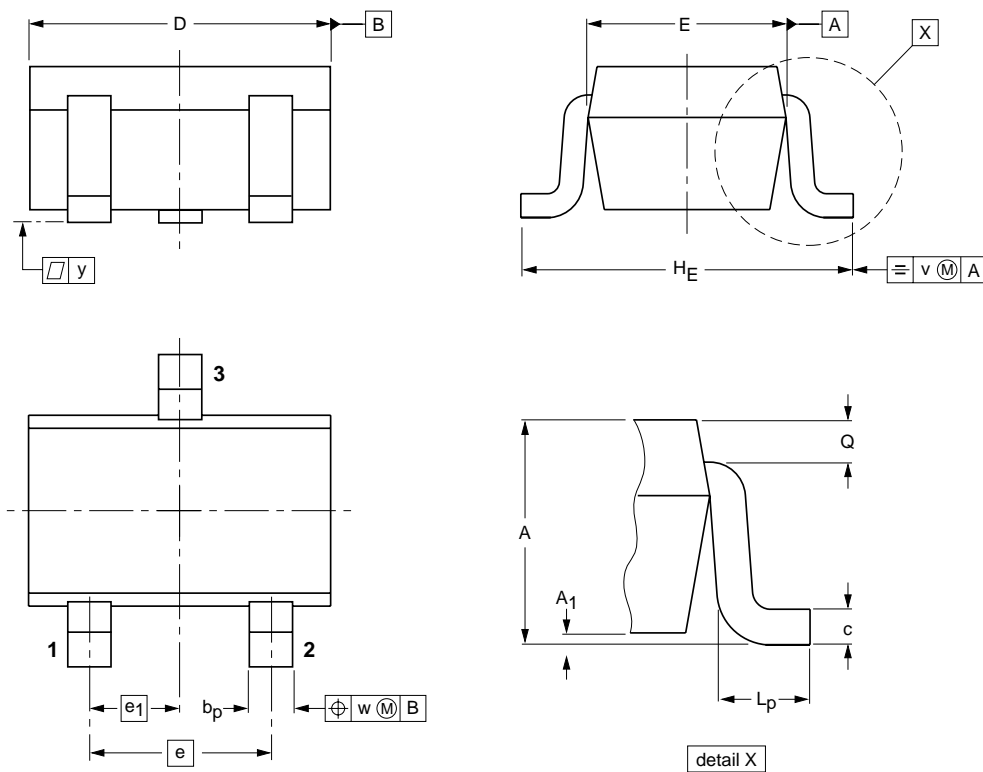


PNP resistor-equipped transistors;
R1 = 2.2 kΩ, R2 = 2.2 kΩ

PDTA123E series

Plastic surface-mounted package; 3 leads

SOT323



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁ max	b _p	c	D	E	e	e ₁	H _E	L _p	Q	v	w
mm	1.1 0.8	0.1	0.4 0.3	0.25 0.10	2.2 1.8	1.35 1.15	1.3	0.65	2.2 2.0	0.45 0.15	0.23 0.13	0.2	0.2

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT323			SC-70			04-11-04 06-03-16